#### TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

# 2SD2499

## HORIZONTAL DEFLECTION OUTPUT FOR COLOR TV

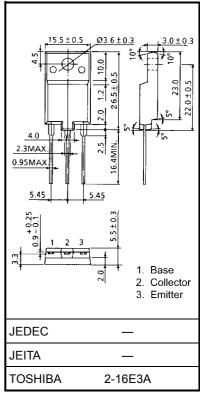
Unit: mm

• Bult-in Damper Type

• Collector Metal (Fin) is Fully Covered with Mold Resin.

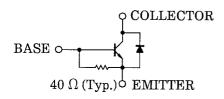
## **MAXIMUM RATINGS (Tc = 25°C)**

| CHARACTERISTIC              |       | SYMBOL           | RATING  | UNIT |  |
|-----------------------------|-------|------------------|---------|------|--|
| Collector-Base Voltage      |       | $V_{CBO}$        | 1500    | V    |  |
| Collector-Emitter Voltage   |       | V <sub>CEO</sub> | 600     | V    |  |
| Emitter-Base Voltage        |       | V <sub>EBO</sub> | 5       | V    |  |
| Collector Current           | DC    | IC               | 6       | А    |  |
|                             | Pulse | I <sub>CP</sub>  | 12      |      |  |
| Base Current                |       | Ι <sub>Β</sub>   | 3       | Α    |  |
| Collector Power Dissipation |       | PC               | 50      | W    |  |
| Junction Temperature        |       | Tj               | 150     | °C   |  |
| Storage Temperature Range   |       | T <sub>stg</sub> | -55~150 | °C   |  |



Weight: 5.5 g (typ.)

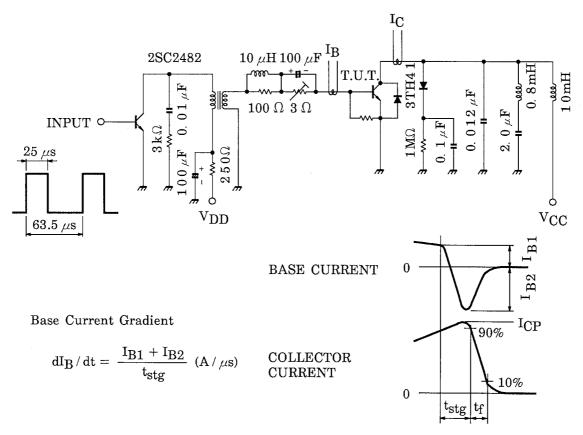
## **EQUIVALENT CIRCUIT**

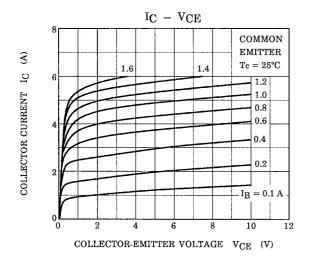


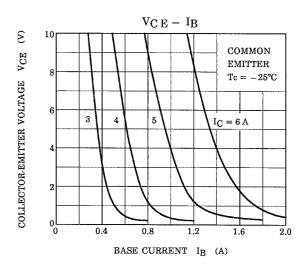
# **ELECTRICAL CHARACTERISTICS (Tc = 25°C)**

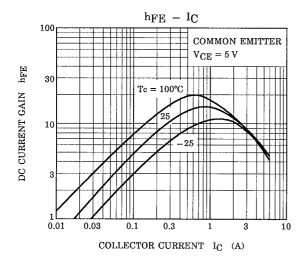
| CHARACTERISTIC                       |              | SYMBOL                | TEST CONDITION   | MIN | TYP. | MAX | UNIT |
|--------------------------------------|--------------|-----------------------|--|-----|------|-----|------|
| Collector Cut-off Current            |              | I <sub>CBO</sub>      | V <sub>CB</sub> = 1500 V, I <sub>E</sub> = 0                                       | _   | _    | 1   | mA   |
| Emitter Cut-off Current              |              | I <sub>EBO</sub>      | V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0  | 67  | _    | 200 | mA   |
| Emitter-Base Breakdown Voltage       |              | V (BR) EBO            | I <sub>C</sub> = 400 mA, I <sub>B</sub> = 0  | 5   | _    | _   | V    |
| DC Current Gain                      |              | h <sub>FE (1)</sub>   | V <sub>CE</sub> = 5 V, I <sub>C</sub> = 1 A  | 8   | _    | 25  | _    |
|                                      |              | h <sub>FE (2)</sub>   | V <sub>CE</sub> = 5 V, I <sub>C</sub> = 4 A  | 5   | _    | 9   |      |
| Collector-Emitter Saturation Voltage |              | V <sub>CE (sat)</sub> | I <sub>C</sub> = 4A, I <sub>B</sub> = 0.8 A  | _   | _    | 5   | V    |
| Base-Emitter Saturation Voltage      |              | V <sub>BE (sat)</sub> | I <sub>C</sub> = 4 A, I <sub>B</sub> = 0.8 A                                       | _   | 1.05 | 1.3 | V    |
| Forward Voltage<br>(Damper Diode)    |              | V <sub>F</sub>        | I <sub>F</sub> = 6 A   | _   | 1.6  | 2.0 | V    |
| Transition Frequency                 |              | f <sub>T</sub>        | V <sub>CE</sub> = 10 V, I <sub>C</sub> = 0.1 A                                     | _   | 2    | _   | MHz  |
| Collector Output Capacitance         |              | C <sub>ob</sub>       | V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz                              | _   | 95   | _   | pF   |
| Switching Time<br>(Fig.1)            | Storage Time | t <sub>stg</sub>      | I <sub>CP</sub> = 4 A, I <sub>B1</sub> (end) = 0.8 A<br>f <sub>H</sub> = 15.75 kHz | _   | 7.5  | 11  | - μs |
|                                      | Fall Time    | t <sub>f</sub>        |  | _   | 0.3  | 0.6 |      |

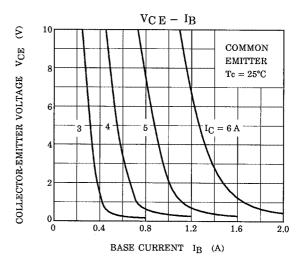
## Fig.1 SWITCHING TIME TEST CIRCUIT

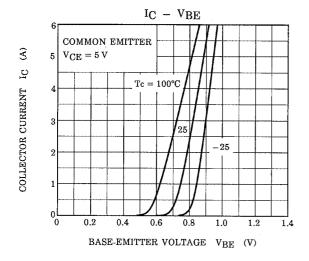


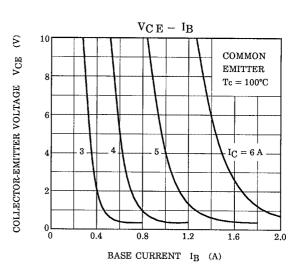




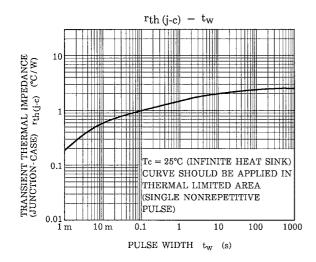


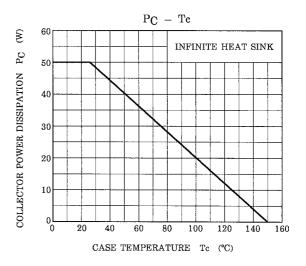


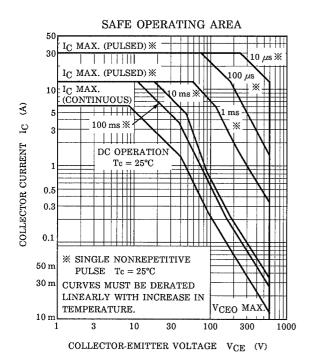




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